



### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
-20V	160m $\Omega$ @-4.5V	-1.9A
	217m $\Omega$ @-2.5V	

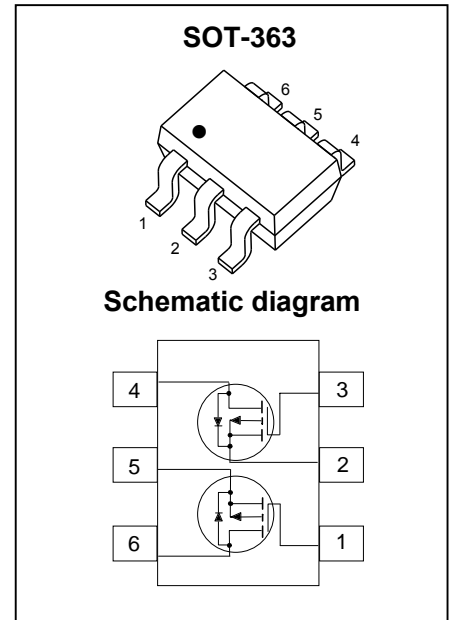
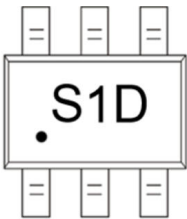
### Feature

- Trench Technology Power MOSFET
- Low  $R_{DS(ON)}$
- Low Gate Charge

### Application

- Load Switch
- DC/DC Converter

### MARKING:



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	$V_{DS}$	-20	V
Gate - Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current <sup>1,5</sup>	$I_D$	-1.9	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	-7.6	A
Power Dissipation <sup>4,5</sup>	$P_D$	0.96	W
Thermal Resistance from Junction to Ambient <sup>5</sup>	$R_{\theta JA}$	130	$^\circ\text{C/W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$

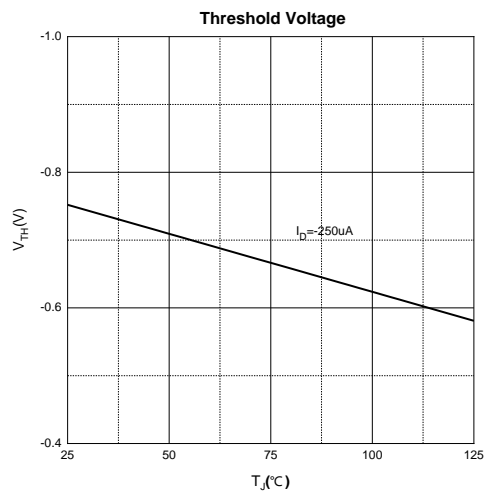
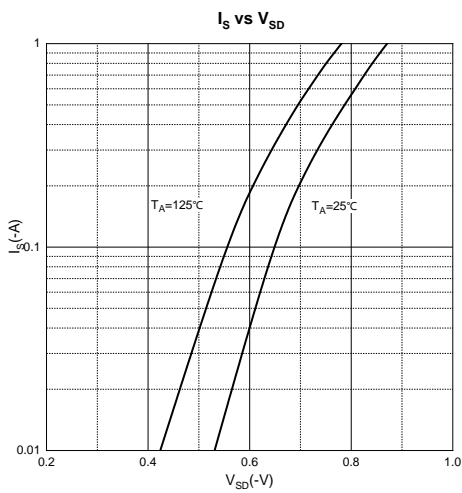
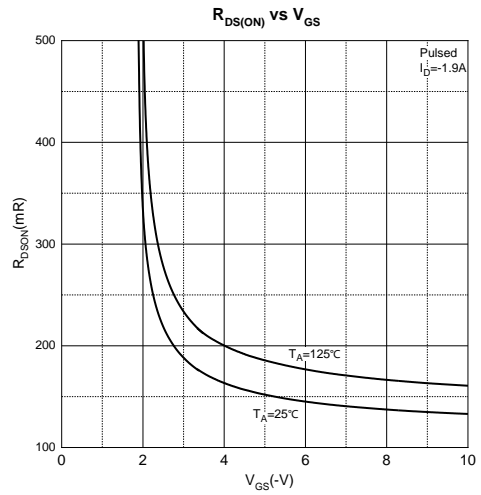
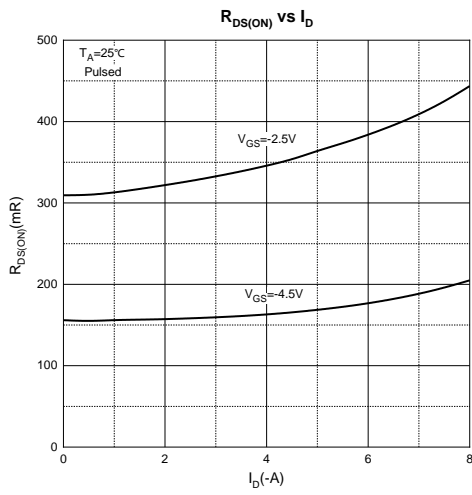
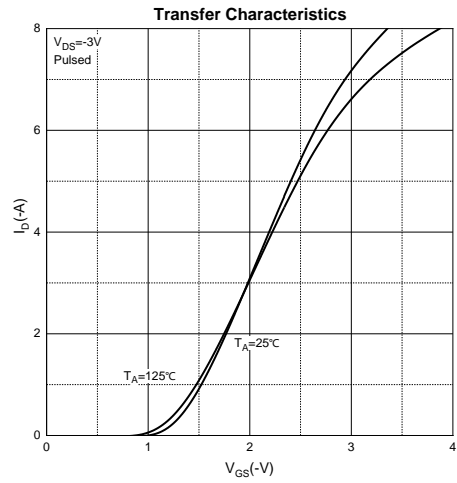
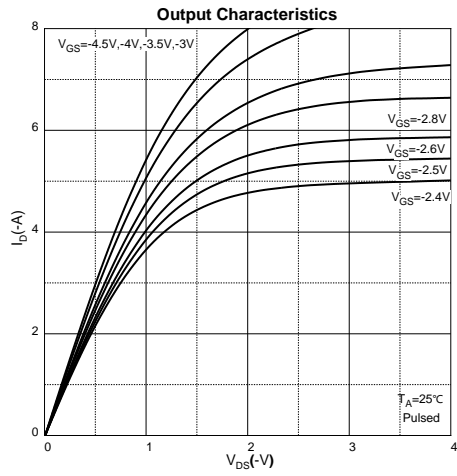
## MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -20V, V_{GS} = 0V$			-1	$\mu A$
Gate - Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0V$			$\pm 100$	nA
<b>On Characteristics<sup>3</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.75	-1	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -1.9A$		160	190	m $\Omega$
		$V_{GS} = -2.5V, I_D = -1.7A$		217	260	
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		273		pF
Output Capacitance	$C_{oss}$			40		
Reverse Transfer Capacitance	$C_{rss}$			25		
Gate Resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		128		$\Omega$
<b>Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = -10V, V_{GS} = -4.5V, I_D = -1.9A$		2.5		nC
Gate-source Charge	$Q_{gs}$			0.4		
Gate-drain Charge	$Q_{gd}$			0.6		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -10V, V_{GS} = -10V,$ $R_L = 5\Omega, R_G = 3\Omega$		11		ns
Turn-on Rise Time	$t_r$			5.5		
Turn-off Delay Time	$t_{d(off)}$			22		
Turn-off Fall Time	$t_f$			8		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>3</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = -0.8A$			-1.2	V

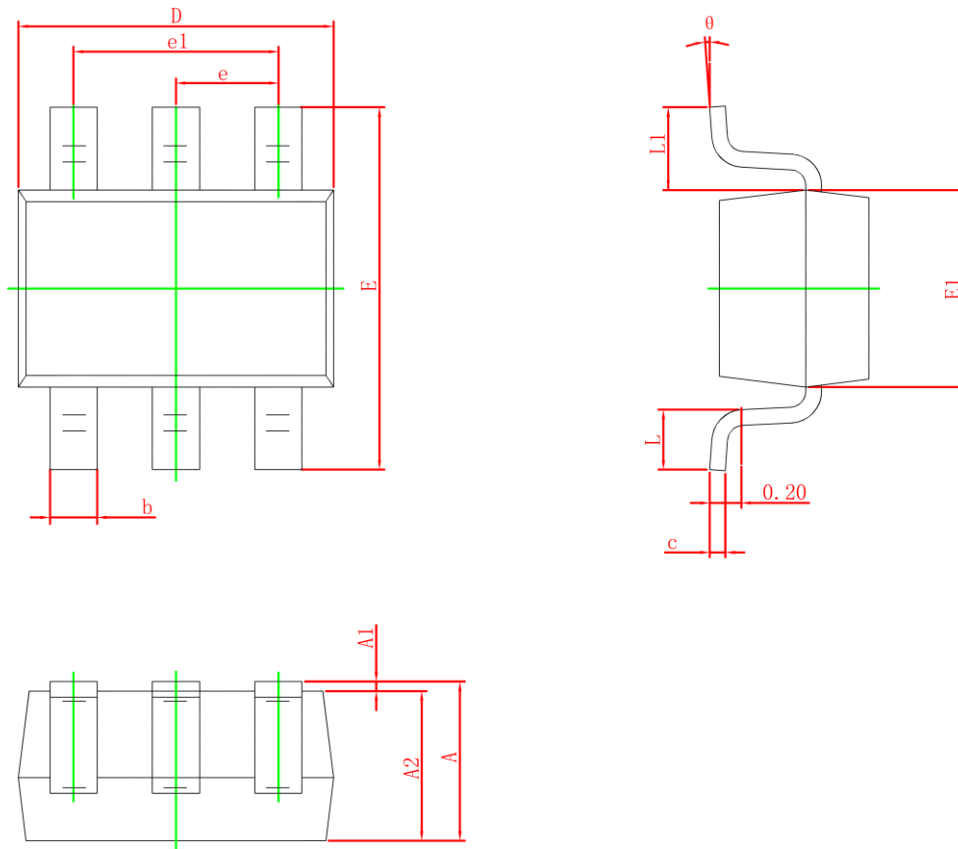
Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width  $\leq 10\mu s$ , duty cycle  $\leq 1\%$ .
- 3.Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- 4.The power dissipation  $P_D$  is limited by  $T_{J(MAX)} = 150^\circ\text{C}$ .
- 5.Device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

**Typical Characteristics**



## SOT-363 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A1	0	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.080	0.150	0.003	0.006
D	1.800	2.200	0.071	0.087
E	2.000	2.450	0.079	0.096
E1	1.150	1.350	0.045	0.053
e	0.650TYP		0.026TYP	
e1	1.200	1.400	0.047	0.055
L1	0.525REF		0.021REF	
L	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°